General Purpose Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter – Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ic	200	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

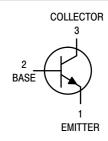
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

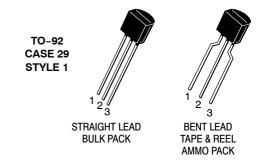
1. Indicates Data in addition to JEDEC Requirements.



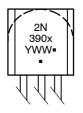
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAMS



x = 3 or 4

Y = Year

WW = Work Week
■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

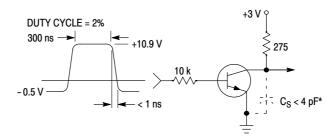
	Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERIS	STICS					
Collector - Emitter B	reakdown Voltage (Note 2) ($I_C = 1.0 \text{ mAdc}, I_B = 0$))	V _{(BR)CEO}	40	-	Vdc
Collector - Base Bre	akdown Voltage (I _C = 10 μAdc, I _E = 0)		V _{(BR)CBO}	60	-	Vdc
Emitter - Base Break	xdown Voltage (I _E = 10 μAdc, I _C = 0)		V _{(BR)EBO}	6.0	-	Vdc
Base Cutoff Current	(V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)		I _{BL}	_	50	nAdc
Collector Cutoff Curi	rent (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)		I _{CEX}	-	50	nAdc
ON CHARACTERIS	TICS			1		1
DC Current Gain (No (I _C = 0.1 mAdc, V _{CE}	2N3903	h _{FE}	20	_	-	
(I _C = 1.0 mAdc, V _{CE}	= 1.0 Vdc)	2N3904 2N3903		40 35	_	
$(I_C = 10 \text{ mAdc}, V_{CE})$	= 1.0 Vdc)	2N3904 2N3903 2N3904		70 50 100	150 300	
(I_C = 50 mAdc, V_{CE}	= 1.0 Vdc)	2N3903		30	_	
$(I_C = 100 \text{ mAdc}, V_{CE})$	= 1.0 Vdc)	2N3904 2N3903 2N3904		60 15 30	- - -	
Collector – Emitter S ($I_C = 10 \text{ mAdc}, I_B = I_C = 10 \text{ mAdc}, I_B = I_C = 10 \text{ mAdc}$			V _{CE(sat)}	- -	0.2 0.3	Vdc
Base – Emitter Satur ($I_C = 10 \text{ mAdc}$, $I_B = 10 \text{ mAdc}$)	ation Voltage (Note 2) 1.0 mAdc) 5.0 mAdc)	V _{BE(sat)}	0.65	0.85 0.95	Vdc	
SMALL-SIGNAL C	HARACTERISTICS	<u>'</u>		1	·I.	- L
Current – Gain – Bar (I _C = 10 mAdc, V _{CE}	ndwidth Product = 20 Vdc, f = 100 MHz)	2N3903 2N3904	f _T	250 300	- -	MHz
Output Capacitance	(V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	-	4.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}	_	8.0	pF
Input Impedance (I _C = 1.0 mAdc, V _{CE}	= 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h _{ie}	1.0 1.0	8.0 10	kΩ
Voltage Feedback R (I _C = 1.0 mAdc, V _{CE}	atio = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h _{re}	0.1 0.5	5.0 8.0	X 10 ⁻⁴
Small-Signal Currer (I _C = 1.0 mAdc, V _{CE}	nt Gain = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h _{fe}	50 100	200 400	-
Output Admittance (h _{oe}	1.0	40	μmhos	
Noise Figure ($I_C = 100 \mu Adc, V_{CE}$	2N3903 2N3904	NF	_ _	6.0 5.0	dB	
SWITCHING CHAR	ACTERISTICS	'		•		
Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = 0.5 Vdc,		t _d	-	35	ns
Rise Time	$I_C = 10 \text{ mAdc}, I_{B1} = 1.0 \text{ mAdc})$		t _r	-	35	ns
Storage Time	(V _{CC} = 3.0 Vdc, I _C = 10 mAdc, I _{B1} = I _{B2} = 1.0 mAdc)	2N3903 2N3904	t _s	- -	175 200	ns
Fall Time			t _f	_	50	ns

Fall Time
2. Pulse Test: Pulse Width \leq 300 μ s; Duty Cycle \leq 2%.

ORDERING INFORMATION

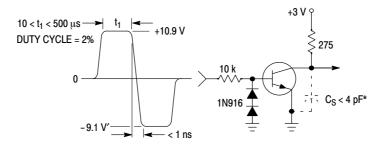
Device	Package	Shipping [†]
2N3903RLRM	TO-92	2000 / Ammo Pack
2N3904	TO-92	5000 Units / Bulk
2N3904G	TO-92 (Pb-Free)	5000 Units / Bulk
2N3904RLRA	TO-92	2000 / Tape & Reel
2N3904RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904RLRM	TO-92	2000 / Ammo Pack
2N3904RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RLRP	TO-92	2000 / Ammo Pack
2N3904RLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904ZL1	TO-92	2000 / Ammo Pack
2N3904ZL1G	TO-92 (Pb-Free)	2000 / Ammo Pack

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



* Total shunt capacitance of test jig and connectors

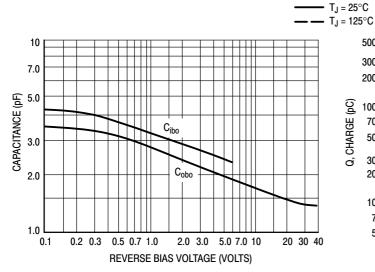
Figure 1. Delay and Rise Time Equivalent Test Circuit



* Total shunt capacitance of test jig and connectors

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS



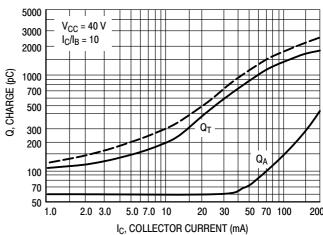
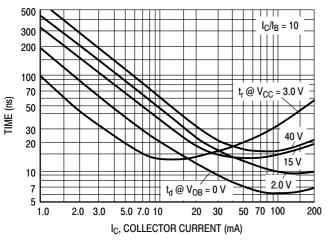


Figure 3. Capacitance

Figure 4. Charge Data



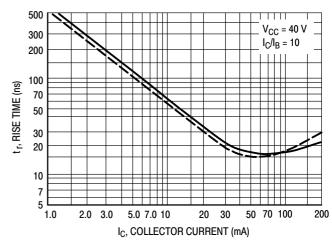
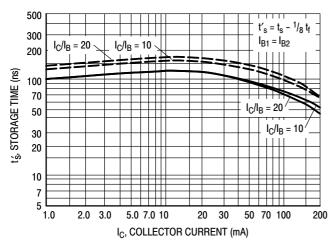


Figure 5. Turn-On Time

Figure 6. Rise Time



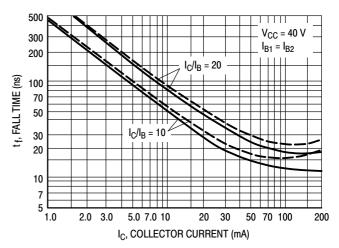
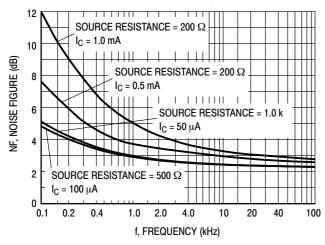


Figure 7. Storage Time

Figure 8. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$



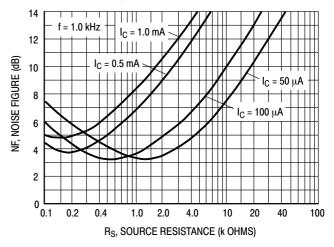
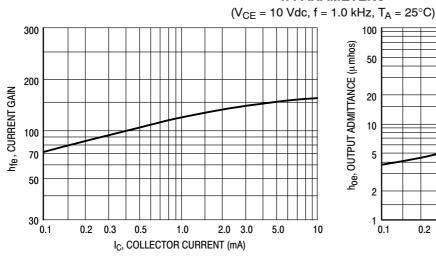


Figure 9.

Figure 10.

h PARAMETERS



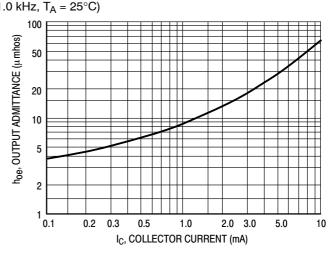
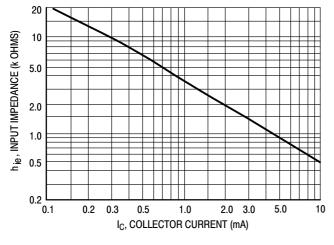


Figure 11. Current Gain

Figure 12. Output Admittance



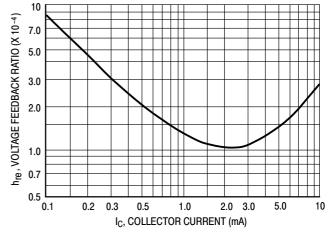


Figure 13. Input Impedance

Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

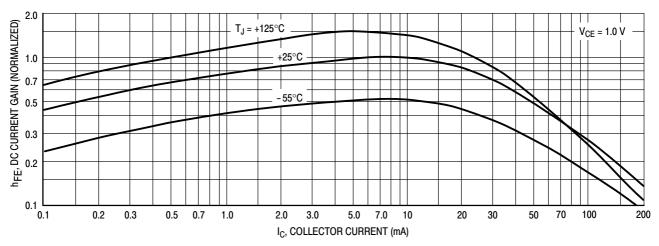


Figure 15. DC Current Gain

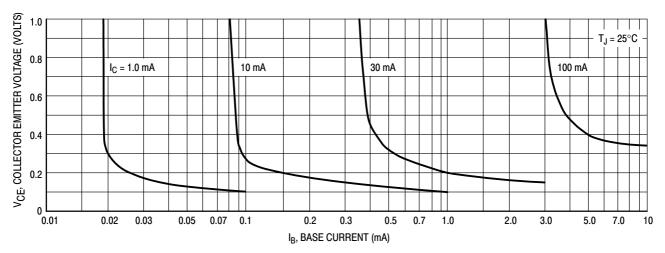


Figure 16. Collector Saturation Region

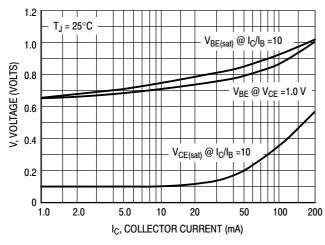


Figure 17. "ON" Voltages

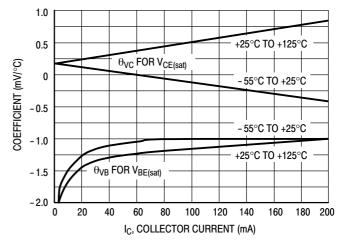
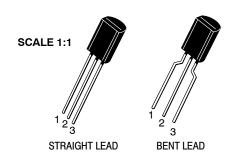
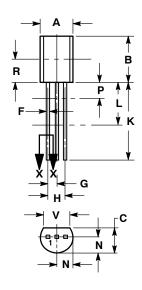


Figure 18. Temperature Coefficients



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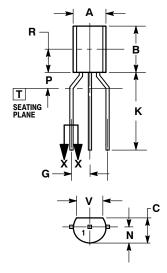
DATE 08 MAY 2012



STRAIGHT LEAD







BENT LEAD



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1994. CONTROLLING DIMENSION: INCHES.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS
- UNCONTROLLED.

 DIMENSION F APPLIES BETWEEN DIMENSIONS P

4.	DIMILI	INIOINI	ALLEILO	DLIVV		VILIVOIV	
	AND L	. DIMEN	ISIONS D	AND J	APPLY	BETWE	EEN DI-
	MENS	IONS L	AND K MIN	MUMIK	THE L	EAD	
	DIMEN	ISIONS	ARE UNC	ONTRO	DLLED I	N DIMI	ENSION
	P AND	BEYON	ND DIMEN	SION K	MINIM	UM.	
				_			

	INC	HES	MILLIN	IETERS
DIM	MIN MAX		MIN	MAX
Α	0.175	0.205	4.44	5.21
В	0.290	0.310	7.37	7.87
С	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.135		3.43	
٧	0.135		3.43	
V	0.135		3.43	

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME
- CONTROLLING DIMENSION: INCHES.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS
- UNCONTROLLED.
 DIMENSION F APPLIES BETWEEN DIMENSIONS P
 AND L. DIMENSIONS D AND J APPLY BETWEEN
 DIMENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.44	5.21
В	0.290	0.310	7.37	7.87
С	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
G	0.094	0.102	2.40	2.80
J	0.018	0.024	0.46	0.61
K	0.500		12.70	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.135		3.43	
٧	0.135		3.43	

STYLES ON PAGE 2

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TO-92 (TO-226) 1 WATT CASE 29-10

ISSUE A

DATE 08 MAY 2012

STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	STYLE 4: PIN 1. 2. 3.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	DRAIN SOURCE GATE
	GATE SOURCE & SUBSTRATE DRAIN	STYLE 7: PIN 1. 2. 3.	SOURCE DRAIN GATE	STYLE 8: PIN 1. 2. 3.	DRAIN GATE SOURCE & SUBSTRATE	STYLE 9: PIN 1. 2. 3.	BASE 1 EMITTER BASE 2	STYLE 10: PIN 1. 2. 3.	CATHODE GATE ANODE
2.	ANODE CATHODE & ANODE CATHODE	STYLE 12: PIN 1. 2. 3.	MAIN TERMINAL 1 GATE MAIN TERMINAL 2	STYLE 13: PIN 1. 2. 3.	ANODE 1 GATE CATHODE 2	STYLE 14: PIN 1. 2. 3.	EMITTER COLLECTOR BASE	STYLE 15: PIN 1. 2. 3.	ANODE 1 CATHODE ANODE 2
PIN 1. 2.	ANODE	PIN 1.	COLLECTOR BASE EMITTER	STYLE 18: PIN 1. 2. 3.	ANODE	STYLE 19: PIN 1. 2. 3.	GATE ANODE CATHODE	2.	NOT CONNECTED CATHODE ANODE
PINI 1	COLLECTOR EMITTER BASE	PIN 1.	SOURCE	PIN 1.	GATE	PIN 1. 2.	EMITTER	PIN 1. 2.	MT 1
	V _{CC} GROUND 2 OUTPUT	STYLE 27: PIN 1. 2. 3.	MT SUBSTRATE MT	2.	CATHODE ANODE GATE	2.	NOT CONNECTED ANODE CATHODE	2.	DRAIN GATE SOURCE
PIN 1. 2.	GATE DRAIN SOURCE	PIN 1.	BASE	PIN 1. 2.	RETURN INPUT OUTPUT	PIN 1. 2.	INPUT GROUND LOGIC		

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